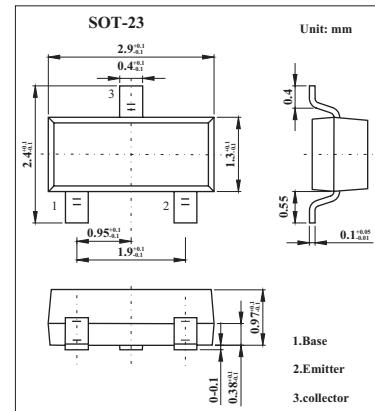


PNP Silicon AF Transistors

KC808(BC808)

■ Features

- High collector current.
- High current gain.
- Low collector-emitter saturation voltage.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	-30	V
Collector-emitter voltage	V _{CEO}	-25	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current (DC)	I _C	-800	mA
power dissipation	P _D	310	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-65 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-to-base breakdown voltage	V _{CBO}	I _C = -10 μ A, V _{BE} = 0	-30			V
Collector-to-emitter breakdown voltage	V _{CEO}	I _C = -10 mA, I _B = 0	-25			V
Emitter-to-base breakdown voltage	V _{EBO}	I _E = -10 μ A, I _C = 0	-5			V
Collector cutoff current	I _{CES}	V _{CB} = -25 V, V _{BE} = 0			-100	nA
Emitter cutoff current	I _{EBO}	V _{EB} = -4 V, I _C = 0			-100	nA
DC current gain *	h _{FE}	I _C = -100 mA, V _{CE} = -1 V	100		630	
		I _C = -300 mA, V _{CE} = -1 V	60			
Collector saturation voltage *	V _{CE(sat)}	I _C = -500 mA, I _B = -50 mA			-0.7	V
Base emitter on voltage	V _{BE(on)}	V _{CE} =-1V, I _C =300mA			-1.2	V
Output Capacitance	C _{ob}	V _{CB} =-10V, f=1MHz			12	pF
Transition frequency	f _T	I _C = -10 mA, V _{CE} = -5 V, f = 50 MHz		100		MHz

* Pulsed: PW ≤ 350 μs, duty cycle ≤ 2%

■ Marking

NO.	KC808-16	KC808-25	KC808-40
Marking	9GA	9GB	9GC
hFE	100 ~250	160~400	250~630